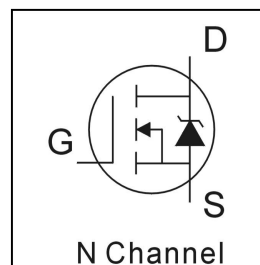


N Channel Power MOSFET with extremely low $R_{DS(on)}$ **Chip Specification****General Description:**

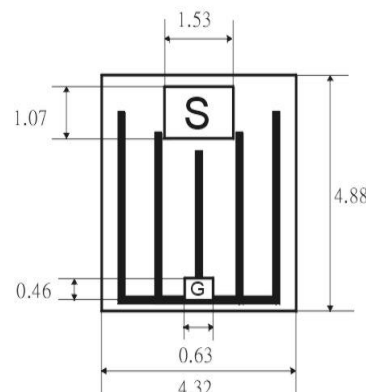
- * Advanced Process Technology
- * Dynamic dV/dt Rating
- * **175°C Operating Temperature**
- * **Fast Switching**
- * **Fully Avalanche Rated**
- * **Extremely low $R_{DS(on)}$**

**Mechanical Data:****D20**Dimension **4.32mm x 4.88mm**Thickness: **400 μm**

Metallization:

Top : : **Al**Backside : **CrNiAg / Au**

Suggested Bonding Conditions:

Die Mounting: **Solder Perform****95/5 PbSn or 92.5/2.5/5 PbAgIn**Source Bonding Wire: **15 mil Al****D20****100V, N Channel****Absolute Maximum Rating**@ $T_a=25^\circ\text{C}$

Characteristics	Symbol	Limit	Unit	Test Conditions
Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	100	V	$V_{GS}=0V$, $I_D=250\mu A$
Static Drain-to - Source On-resistance	$R_{DS(ON)}$	0.077	Ω	$V_{GS}=10V$, $I_D=9A$
Continuous Drain current (in target package)	$I_D@25^\circ\text{C}$	18	A	$V_{GS}=10V$
Continuous Drain current (in target package)	$I_D@100^\circ\text{C}$	11	A	$V_{GS}=10V$
Operation Junction	T_j	-55~175	$^\circ\text{C}$	
Storage Temperature	T_{STR}	-55~175	$^\circ\text{C}$	

Target Device: IRF540

TO-220AB

 P_D

125

W

@ $T_c=25^\circ\text{C}$